



13/D (WE)
Amend D
Y. Robinson
4/25/03
501.39149X00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: NAKAMURA et al.
Serial No.: 09/708,450
Filed: November 9, 2000
For: A SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE
AND THE METHOD THEREOF
Group: 2811
Examiner: D. Owens

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entered
J. Robinson
5/31/03

AMENDMENT AFTER FINAL REJECTION

BOX AF

Commissioner for Patents
Washington, D.C. 20231

April 21, 2003

Sir:

In response to the Office Action dated November 20, 2002, please amend the above-identified application as follows.

IN THE CLAIMS:

Please cancel claims 23 and 27 without prejudice or disclaimer.

Please amend claims 20-22, 24-26 and 28-34 as follows:

20. (Twice Amended) A method of producing a semiconductor integrated circuit device comprising the steps of:

(a) forming bit lines and a first layer wiring over MISFET on a main plane of a semiconductor substrate through a first inter-layer insulating film, forming a second inter-layer insulating film and an electrode-forming insulating film, and etching holes in said electrode-forming insulating film;

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